

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L23	1237	257/355.ccls. and (resist\$6) and (semiconductor silicon germanium) and substrate	US-PGPUB; USPAT	OR	ON	2007/11/08 11:03
L22	1578	257/355.ccls.	US-PGPUB; USPAT	OR	ON	2007/11/08 10:29
L6	100	(@ad<"20021029" or @rlad<"20021029") and 257/487. ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/11/08 10:28
L21	0	((resistance resistor) and semiconductor and (terminal pad) and substrate and (perimeter (guard adj ring) outer edge) and (display) and (electrode conductor metal)).clm. not I20	US-PGPUB; USPAT	OR	ON	2007/11/08 10:27
L20	59	((resistance resistor) and semiconductor and (terminal pad) and substrate and (perimeter (guard adj ring) outer edge) and (emit\$5 display) and (electrode conductor metal)).clm.	US-PGPUB; USPAT	OR	ON	2007/11/08 10:27
S42	59	((resistance resistor) and semiconductor and (terminal pad) and substrate and (perimeter (guard adj ring) outer edge) and (emit\$5 display) and (electrode conductor metal)).clm.	US-PGPUB; USPAT	OR	ON	2007/11/08 10:13
L19	255	(@ad<"20021029" or @rlad<"20021029") and 361/90. ccls. and (resistance resistor) and (semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/11/08 10:06
S43	595	(@ad<"20021029" or @rlad<"20021029") and 257/358, 360.ccls. and (resistance resistor) and (semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/11/08 10:03

EAST Search History

L14	24	("5218222" "5270565" "5293057" "5336908" "5430602" "5581104" "5654860" "5656967" "5717559" "5721658" "5744839" "5767552" "5805009" "5880917" "5889644" "5982599" "6004838" "6040733" "6130811" "6137664" "6181540" "6204537" "6678133" "RE36024").PN. OR ("6967826").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/11/08 09:23
L13	2	("5034796").PN. OR ("5635822").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/11/08 09:20
L12	3	"5635822"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/08 09:19
L11	11	("4692781" "5229635" "5512783" "5623387" "5646434" "5712753" "5715127" "5818086").PN. OR ("6246122").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/11/08 09:11
L9	21	("4819047" "4870530" "4878145" "5012317" "5034845" "5159518" "5515225").PN. OR ("5715127").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/11/08 09:06
S5	99	(@ad<"20021029" or @rlad<"20021029") and 257/487. ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/11/08 08:41
L5	73	(@ad<"20021029" or @rlad<"20021029") and 257/489. ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor layer substrate silicon first second electric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/08 08:36
S6	64	(@ad<"20021029" or @rlad<"20021029") and 257/489. ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/11/08 08:35

EAST Search History

S33	588	(@ad<"20021029" or @rlad<"20021029") and 257/358, 360.ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/11/08 08:33
L2	95	(@ad<"20021029" or @rlad<"20021029") and 323/273. ccls. and semiconductor and resist\$6	US-PGPUB; USPAT	OR	ON	2007/11/08 08:32
S37	242	(@ad<"20021029" or @rlad<"20021029") and 323/273. ccls.	US-PGPUB; USPAT	OR	ON	2007/11/08 08:31
S44	1	"20040100608"	US-PGPUB; USPAT	OR	ON	2007/11/07 16:27
S41	1	("5635822").URPN.	USPAT	OR	ON	2007/06/19 14:55
S40	6	("4475119" "4649416" "4783697" "5034796" "5111069" "5250821").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/19 14:55
S39	12	("5034796").URPN.	USPAT	OR	ON	2007/06/19 14:53
S38	2	("5034796").PN. OR ("5635822").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/19 14:52
S36	653	(@ad<"20031002" or @rlad<"20031002") and 257/72. ccls. and emit\$ and electrode and (edge perimeter side periphery)	US-PGPUB; USPAT	OR	ON	2007/06/18 10:41
S35	1905	(@ad<"20031002" or @rlad<"20031002") and 257/72. ccls.	US-PGPUB; USPAT	OR	ON	2007/06/18 10:37
S34	55	(@ad<"20031002" or @rlad<"20031002") and 257/358, 360.ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not S33	US-PGPUB; USPAT	OR	ON	2007/06/18 10:33
S32	281	(@ad<"20031002" or @rlad<"20031002") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not S31	US-PGPUB; USPAT	OR	ON	2007/02/23 12:41

EAST Search History

S31	1907	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:40
S3	1907	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:40
S30	28	(@ad<"20031002" or @rlad<"20031002") and pad and (guard adj ring) and (chip or substrate) and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not S29	US-PGPUB; USPAT	OR	ON	2007/02/23 12:37
S29	144	(@ad<"20021029" or @rlad<"20021029") and pad and (guard adj ring) and (chip or substrate) and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:37
S28	6	(@ad<"20031002" or @rlad<"20031002") and (((pad adj pad) ("pad to pad"))) with (resistance resistor))and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not S27	US-PGPUB; USPAT	OR	ON	2007/02/23 12:36
S4	144	(@ad<"20021029" or @rlad<"20021029") and pad and (guard adj ring) and (chip or substrate) and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:36

EAST Search History

S27	172	(@ad<"20021029" or @rlad<"20021029") and (((pad adj pad) ("pad to pad"))) with (resistance resistor))and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:34
S10	172	(@ad<"20021029" or @rlad<"20021029") and (((pad adj pad) ("pad to pad"))) with (resistance resistor))and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:34
S26	5964	(@ad<"20021029" or @rlad<"20021029") and (((glass adj substrate) (insulat\$5 adj substrate))) and (pad terminal) and (substrate) and (device transistor tft) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) and (lcd "liquid crystal") and semiconductor	US-PGPUB; USPAT	OR	ON	2007/02/23 12:30
S9	3057	(@ad<"20021029" or @rlad<"20021029") and ((pad adj pad) ("pad to pad")) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:22
S20	22	("4819047" "5173755" "5237395" "5641981").PN. OR ("5917220").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/22 16:14
S12	9	("4982079").PN. OR ("5736732").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/22 08:35
S11	2	("5034796").PN. OR ("5635822").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/21 14:44

EAST Search History

S8	44	("3676742" "3813639" "4331948" "4436183" "4486738" "4586105" "4726991" "4729752" "4770738" "4788523" "4813891" "4819047" "4928199" "4939619" "4945395" "4977357" "4992333" "5008770" "5029041" "5068634" "5089929" "5099380" "5101317" "5130881" "5142263" "5175662" "5183698" "5189387" "5194010" "5195010" "5197891" "5208723" "5216404" "5229037" "5246388" "5248517" "5260848" "5262754" "5278535" "5294374" "5301084" "5315472" "5340641" "5342220" "5393597" "5416662" "5444593" "5483407" "5515226" "5578867" "5674083" "5715127" "5796570").PN. OR ("6064094"). URPN.) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) and (@ad<"20021029" or @rlad<"20021029")	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/21 13:13
S7	57	("3676742" "3813639" "4331948" "4436183" "4486738" "4586105" "4726991" "4729752" "4770738" "4788523" "4813891" "4819047" "4928199" "4939619" "4945395" "4977357" "4992333" "5008770" "5029041" "5068634" "5089929" "5099380" "5101317" "5130881" "5142263" "5175662" "5183698" "5189387" "5194010" "5195010" "5197891" "5208723" "5216404" "5229037" "5246388" "5248517" "5260848" "5262754" "5278535" "5294374" "5301084" "5315472" "5340641" "5342220" "5393597" "5416662" "5444593" "5483407" "5515226" "5578867" "5674083" "5715127" "5796570").PN. OR ("6064094"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/21 13:12

EAST Search History

S2	1981	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 10:46
S1	1981	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 10:38